

Understanding ESD protection device characteristics Basic introduction

## Basic application examples



Fig. 1 Bidirectional ESD protection


Fig. 2 Unidirectional ESD protection

Bidirectional ESD protection devices are symmetric (fig. 1). They can be used on the lines with bipolar signals $\left(-\mathrm{V}_{\text {WM }} \leq \mathrm{V}_{\text {signal }} \leq \mathrm{V}_{\text {wM }}\right)$ as well as with unipolar signals ( $\left.0 \leq \mathrm{V}_{\text {signal }} \leq \mathrm{V}_{\text {WM }}\right)$.

Unidirectional ESD protection devices (fig. 2) are asymmetric, and can be used on lines with unipolar signals only ( $0 \leq \mathrm{V}_{\text {signal }} \leq \mathrm{V}_{\text {wM }}$ ). Physically they are used in reverse direction, analogous to Zener diodes. The convention across the industry is to specify voltage and current in that direction as positive, like the voltages in the application.

Types of current-voltage (I-V) characteristic curves (not to scale)


Fig. 3 Diode-like


Fig. 4 Mild snapback


Fig. 5 Strong snapback (SCR ${ }^{11}$, thyristor)

Current-voltage (I-V) characteristic summary

| I-V behaviour type | Features and benefits | Best suited for |
| :---: | :---: | :---: |
| Diode-like | > Simple behavior, easy to use <br> > Good protection performance <br> > Low voltage overshoot, fast turn-on | > Fast turn-on applications <br> > Multi-purpose and low speed applications: buttons, switches, audio, GPIO, touch panels... |
| Mild snapback | > Improved protection performance $\left(\mathrm{V}_{\mathrm{cl}}\right)$ <br> > Enables low capacitance ( $C_{L}$ ) <br> > Excellent balance of $V_{w m}$ and $V_{c l}$ | Same applications as diode-like, plus > High speed I/O and RF applications |
| Strong snapback (SCR, thyristor) | ```> "Pound for pound" best protection performance (V) > Enables low capacitance (CL``` | > RF applications <br> > Applications with most demanding $\mathrm{V}_{\mathrm{cl}}$ requirement: <br> - High speed applications, LVDS <br> - Super fine geometry SoC I/O with nm -scale technology |

## Typical first order selection parameters for the TVS

$C_{L}$ - line capacitance - especially important for high speed/RF applications, less so for general purpose and low speed applications.
$\mathrm{V}_{\mathrm{wm}}$ - maximum working voltage - must be chosen equal or higher than the maximum voltage on the protected line during specified operation (see fig. 6). Typical protection devices have $\mathrm{V}_{\mathrm{WM}}$ aligned with standard system and $\mathrm{I} / \mathrm{O}$ voltages $\left(\mathrm{V}_{10}, \mathrm{~V}_{\text {bus }}\right)$, i.e. $2.1 \mathrm{~V}, 3.3 \mathrm{~V}, 5 \mathrm{~V}$.
$\mathrm{V}_{\mathrm{cl}}$ - clamping voltage - the most important parameter for protection performance. At the given stress level $\left(I_{\text {TLP }}, I_{\text {PP }}\right)^{1)} V_{\text {cl }}$ must be lower than the failure voltage of the IC (if known), otherwise as low as possible.


Fig. $6 \mathrm{~V}_{\mathrm{wm}}$ equal or higher than $\mathrm{V}_{\text {signal }}$

## I-V curve parameters for advanced understanding

## $\mathrm{V}_{\mathrm{h}}, \mathrm{I}_{\mathrm{h}}$ - holding voltage, holding current

> For strong snapback devices $\mathrm{V}_{\mathrm{h}}<\mathrm{V}_{\mathrm{wm}}$. $\mathrm{V}_{\mathrm{h}}$ is a local minimum of the voltage, and $\mathrm{I}_{\mathrm{h}}$ is the corresponding current. $\mathrm{V}_{\mathrm{h}}$ and $\mathrm{I}_{\mathrm{h}}$ must be balanced with the line driver DC voltage/ current capability in order to prevent a device latch-up ${ }^{2)}$.
> For mild snapwback devices $\mathrm{V}_{\mathrm{h}}>\mathrm{V}_{\mathrm{w}} \cdot \mathrm{I}_{\mathrm{h}}$ is not given in the datasheet, $\mathrm{V}_{\mathrm{h}}$ is measured at a fixed testing current $\mathbf{I}_{\mathrm{t}}$.
$\mathrm{V}_{\mathrm{br}}$ - breakdown voltage - measured at specified testing current $\mathrm{I}_{\mathrm{t}}$
$\mathrm{V}_{\mathrm{tr}}$ - trigger voltage - maximum voltage before the device turns on (triggers) and snaps back to $\mathrm{V}_{\mathrm{h}}$. For snapback devices $\mathrm{V}_{\mathrm{tr}}$ is slightly higher than $\mathrm{V}_{\mathrm{br}} . \mathrm{V}_{\mathrm{tr}}$ is verified by design.
$I_{L}$ - leakage current - current that flows through the device at $V_{\text {wm }}$
$\mathrm{R}_{\mathrm{dyn}}$ - dynamic resistance - characterizes the steepness of the device I-V characteristic while conducting an ESD event ${ }^{3}$. Lower $\mathrm{R}_{\mathrm{dyn}}$ is usually related to better protection performance, can be used to estimate $\mathbf{V}_{\text {cl }}$ at different stress levels ( $\mathbf{I}_{\text {TLP }}$ ) than datasheet provides.

## Other device parameters/characteristics

Linearity - in applications with RF transmitters, e.g. mobile phones, EMI/EMC can be a concern due to harmonic generation from ESD protection devices on signal lines. ESD protection devices optimized for linearity generate less harmonic distortion and intermodulation.

IL - insertion loss - correlates highly with $\mathrm{C}_{\mathrm{L}}$, important only for high-speed/RF applications
$V_{\text {ESD }}$ - maximum electrostatic discharge voltage - based on IEC61000-4-2
$I_{\text {PP }}$ - maximum pulse current - also referred to as surge robustness,
based on IEC61000-4-5

[^0]Low capacitance ESD protection devices

| Product name | C typical [pF] | $v_{\text {wM }}$ <br> [V] | $\mathrm{V}_{\mathrm{cl}}$ typical <br> @ $\mathrm{I}_{\text {TLP }}=16 \mathrm{~A}$ <br> [V] | $I_{L}$ max <br> [nA] | $\mathrm{R}_{\text {dyn }}$ typical <br> [ $\Omega$ ] | $\mathrm{V}_{\text {ESD }}{ }^{11}$ <br> contact <br> [kV] | $\mathrm{I}_{\mathrm{pp}}{ }^{2)}$ <br> $8 / 20 \mu \mathrm{~s}$ <br> [A] | Availability |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| ESD106-B1-W0201 | 0.13 | 5.5 | 25.0 | 20 | 1.10 | 14 | 1.5 | Mass production |
| ESD107-U1-W0201 | 0.50 | 3.3 | 12.5/4.0 ${ }^{3}$ | 50 | 0.40/0.203) | 20 | 3.0 | In planning |
| ESD108-B1-CSP0201 | 0.28 | 5.5 | 20.0 | 20 | 0.78 | 25 | 2.5 | Mass production |
| ESD119-B1-W01005 | 0.20 | 5.5 | 20.0 | 20 | 0.80 | 25 | 2.5 | Mass production |
| ESD120-B1-W0201 | 0.25 | 2.1 | 19.0 | 200 | 0.94 | 15 | - | Development |
| ESD121-B1-W0201 | 0.25 | 7.0 | 24.0 | 200 | 0.90 | 15 | - | In planning |
| ESD128-B1-W0201 | 0.30 | 18.0 | 32.0 | 30 | 0.85 | 15 | 2.0 | Mass production |
| ESD129-B1-W01005 | 0.30 | 18.0 | 32.0 | 30 | 0.82 | 15 | 2.0 | Mass production |
| ESD130-B1-W0201 | 0.30 | 5.5 | 20.0 | 20 | 0.80 | 18 | 2.5 | Mass production |
| ESD131-B1-W0201 | 0.23 | 5.5 | 13.0 | 100 | 0.66 | 20 | 3.5 | Mass production |
| ESD132-B1-W0201 | 0.45 | 5.5 | 7.0 | 100 | 0.20 | 30 | 9.0 | Mass production |
| ESD133-B1-W01005 | 0.20 | 5.5 | 13.0 | 50 | 0.56 | 20 | 3.0 | Mass production |
| ESD134-B1-W0201 | 0.30 | 2.1 | 7.7 | 20 | 0.28 | 28 | 7.5 | Mass production |
| ESD144-B1-W0201 | 0.20 | 18.0 | 12.5 | 50 | 0.58 | 18 | 3.5 | Mass production |
| ESD145-B1-W01005 | 0.20 | 18.0 | 12.5 | 50 | 0.58 | 18 | 3.5 | Mass production |

Nomenclature - Sales number


ESD1xx low capacitance, $\mathrm{C}_{<}<1 \mathrm{pF}$
ESD2xx multi-purpose, $C_{L}>1 \mathrm{pF}$
B Bidirectional $\qquad$
Unidirectional
$-1$

W01005, CSP01005 wafer-level, $0.4 \mathrm{~mm} \times 0.2 \mathrm{~mm}$ W0201, CSP0201 wafer-level, $0.6 \mathrm{~mm} \times 0.3 \mathrm{~mm}$ 02N

Multi-purpose ESD protection devices

| Product name | $C_{L}$ typical [pF] | $v_{w M}$ <br> [V] | $\mathrm{V}_{\mathrm{ct}}$ typical <br> @ $1_{\text {TLP }}=16 \mathrm{~A}$ <br> [V] | $\begin{aligned} & I_{\text {max }} \\ & {[\text { nA] }} \end{aligned}$ | $\mathrm{R}_{\text {dyn }}$ typical $[\Omega]$ | $\mathrm{V}_{\text {ESD }}{ }^{11}$ <br> contact <br> [kV] | $\begin{array}{\|l\|} \hline \mathrm{I}_{\mathrm{pp}}{ }^{2)} \\ 8 / 20 \mu \mathrm{~s} \end{array}$ $[\mathrm{A}]$ | Availability |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| ESD200-B1-CSP0201 | 6.5 | 5.5 | 13.0 | 100 | 0.20 | 17 | 3.0 | Mass production |
| ESD202-B1-CSP01005 | 6.5 | 5.5 | 13.0 | 100 | 0.20 | 15 | 3.0 | Mass production |
| ESD230-B1-W0201 | 7.0 | 5.5 | 13.0 | 100 | 0.22 | 16 | 3.0 | Mass production |
| ESD231-B1-W0201 | 3.5 | 5.5 | 12.0 | 20 | 0.30 | 30 | 12.0 | Mass production |
| ESD233-B1-W0201 | 33.0 | 5.5 | 13.0 | 100 | 0.20 | 20 | 5.0 | Mass production |
| ESD234-B1-W0201 | 56.0 | 5.5 | 12.5 | 100 | 0.15 | 19 | 7.0 | Mass production |
| ESD237-B1-W0201 | 7.0 | 8.0 | 13.0 | 100 | 0.21 | 16 | 3.0 | Mass production |
| ESD239-B1-W0201 | 3.2 | 22.0 | 27.0 | 100 | 0.27 | 16 | 3.0 | Mass production |
| ESD240-B1-W01005 | 3.0 | 22.0 | 27.0 | 100 | 0.31 | 16 | 3.0 | Development |
| ESD241-B1-W0201 | 6.5 | 3.3 | 6.0 | 30 | 0.09 | 18 | 4.5 | Mass production |
| ESD242-B1-W01005 | 6.0 | 3.3 | 6.0 | 30 | 0.09 | 18 | 4.5 | Mass production |
| ESD245-B1-W0201 | 5.8 | 5.5 | 7.5 | 30 | 0.10 | 15 | 5.5 | Mass production |
| ESD246-B1-W01005 | 5.5 | 5.5 | 7.5 | 30 | 0.10 | 15 | 5.5 | Mass production |
| ESD249-B1-W0201 | 4.2 | 18.0 | 23.5 | 100 | 0.27 | 16 | 3.0 | Mass production |
| ESD251-B1-W0201 | 33.0 | 3.3 | 6.0 | 100 | 0.09 | 25 | 8.0 | Development |
| ESD252-B1-W01005 | 33.0 | 3.3 | 6.0 | 100 | 0.09 | 25 | 8.0 | Development |
| ESD253-B1-W0201 | 2.8 | 24.0 | 31.0 | 100 | 0.30 | 15 | 3.0 | Mass production |
| ESD254-B1-W01005 | 2.5 | 24.0 | 32.0 | 100 | 0.35 | 15 | 3.0 | Development |
| ESD259-B1-W0201 | 4.2 | 16.0 | 24.0 | 500 | 0.29 | 15 | 2.5 | Mass production |
| ESD307-U1-02N | 270.0 | 10.0 | 17.0/2.03) | 100 | 0.05/0.053) | 30 | 34.0 | Mass production |
| ESD311-U1-02N | 210.0 | 15.0 | 22.0/2.03) | 100 | 0.07/0.053 | 30 | 28.0 | Mass production |

1) $V_{\text {ESD }}$ based on IEC61000-4-2, contact discharge
2) I Ipp based on IEC61000-4-5, 8/20 $\mu$ s current waveform
3) Positive/negative direction

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[^0]:    $\mathrm{V}_{\mathrm{cl}}$ depends on the pulse width and shape: TLP, IEC61000-4-2, IEC61000-4-5
    2) AN525: Latch-up prediction for SCR TVS device
    3) Measured using Transmission Line Pulse (TLP) system

